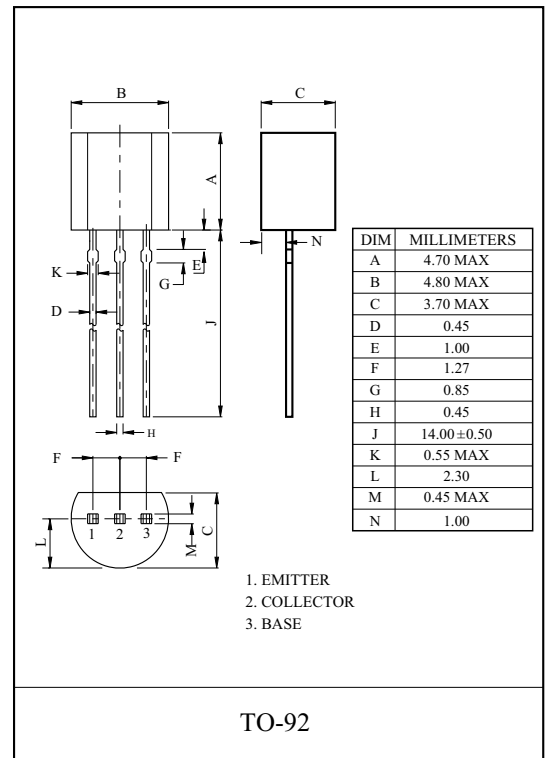


HIGH VOLTAGE APPLICATION.
TELEPHONE APPLICATION.

MAXIMUM RATING (Ta=25 °C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-300	V
Collector-Emitter Voltage	V_{CEO}	-300	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-500	mA
Emitter Current	I_E	500	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 ~ 150	°C

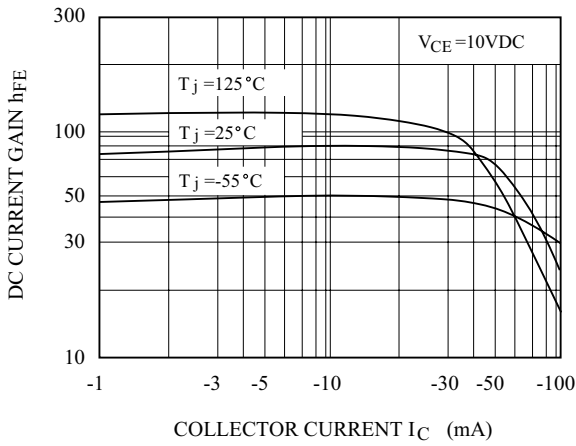


ELECTRICAL CHARACTERISTICS (Ta=25 °C)

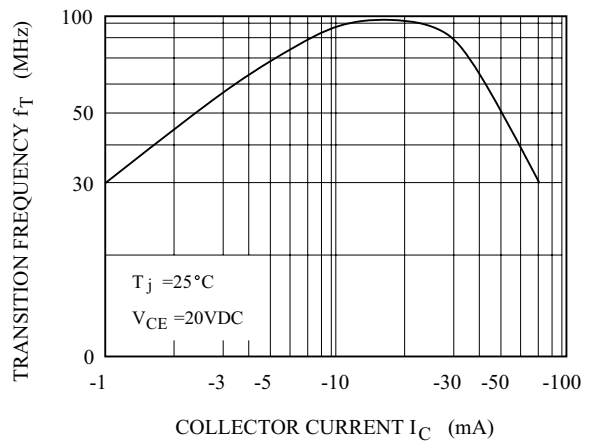
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-300	-	-	V
Emitter Cut-off Current	$V_{(BR)CEO}$	$I_C = -1.0mA, I_B = 0$	-300	-	-	V
DC Current Gain	h_{FE}^*	$I_C = -1.0mA, V_{CE} = -10V$	25	-	-	
		$I_C = -10mA, V_{CE} = -10V$	40	-	-	
		$I_C = -30mA, V_{CE} = -10V$	25	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}^*$	$I_C = -20mA, I_B = -2.0mA$	-	-	-0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}^*$	$I_C = -20mA, I_B = -2.0mA$	-	-	-0.9	V
Transition Frequency	f_T	$V_{CE} = -20V, I_C = -10mA, f = 100MHz$	50	-	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -20V, I_E = 0, f = 1MHz$	-	-	6.0	pF

Note : * Pulse test : $PW \leq 300\mu S, \text{ Duty Cycle} \leq 2\%$

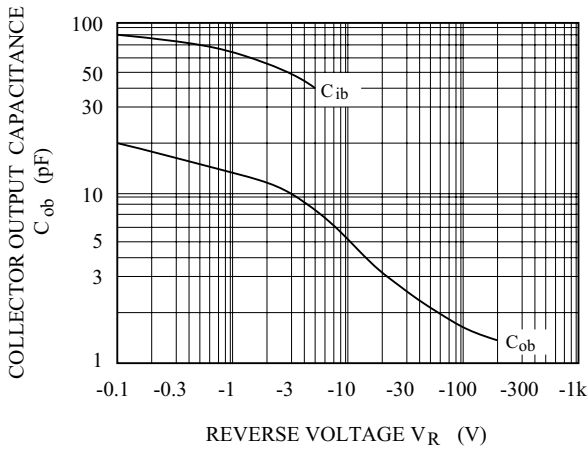
$h_{FE} - I_C$



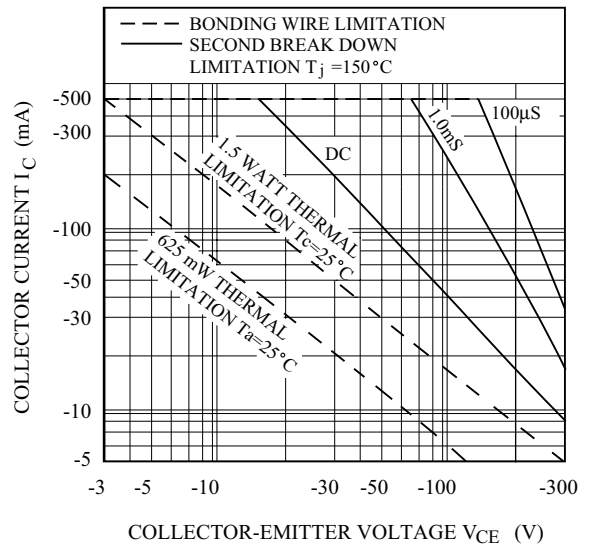
$f_T - I_C$



$C_{ob} - V_R$



$I_C - V_{CE}$



$V_{BE(sat)}, V_{CE(sat)} - I_C$

